

### NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE1540K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

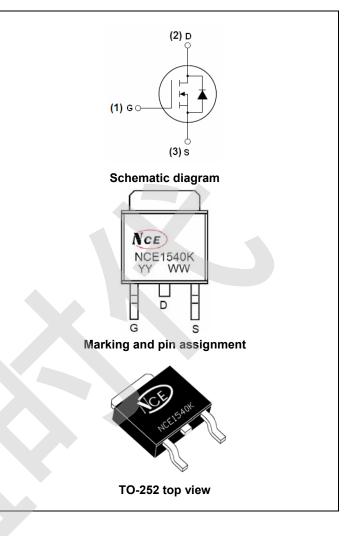
- $V_{DS} = 150V, I_D = 40A$  $R_{DS(ON)} < 45mΩ @ V_{GS} = 10V$  (Typ:35mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1540K	NCE1540K	TO-252	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	150	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	40	А
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	29	Α
Pulsed Drain Current	I <sub>DM</sub>	164	Α
Maximum Power Dissipation	P <sub>D</sub>	140	W
Derating factor		0.93	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	310	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}$ C



# **NCE1540K**

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	1.07	°C/W	
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#### Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	150	170	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.5	3.2	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =18A	-	35	45	mΩ
Forward Transconductance	<b>g</b> Fs	V <sub>DS</sub> =15V,I <sub>D</sub> =18A	38	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	)/ OF)/)/ O)/	-	4200	-	PF
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, F=1.0MHz	-	203	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UMHZ	-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	17.8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30V, $I_{D}$ =2A, $R_{L}$ =15 $\Omega$	-	11.8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =2.5 $\Omega$	-	56	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	14.6	-	nS
Total Gate Charge	Qg	V 20VI 20A		105	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=30V, I_{D}=30A,$ $V_{GS}=10V$		21	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V		31.5	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =18A	-	0.82	1.2	V
Diode Forward Current (Note 2)	Is		-	-	40	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 18A	-	70	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	230	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

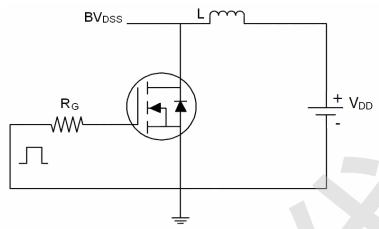
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25  $^{\circ}\text{C},\,V_{DD}\text{=-}50\text{V},V_{G}\text{=-}10\text{V},L\text{=-}0.5\text{mH},Rg\text{=-}25\Omega$

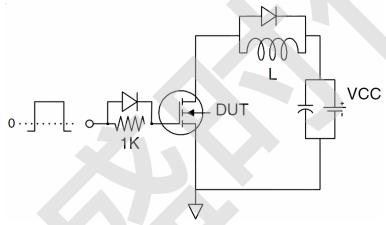


## **Test Circuit**

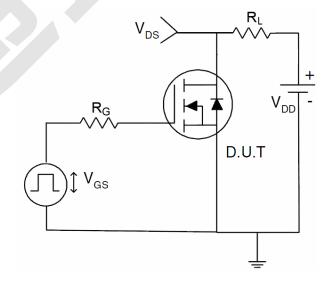
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

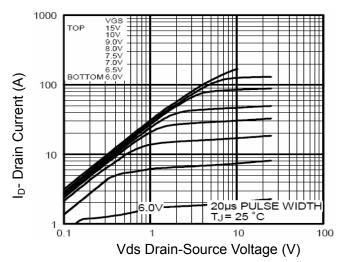


## 3) Switch Time Test Circuit

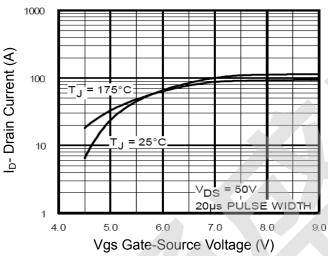




## Typical Electrical and Thermal Characteristics (Curves)



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

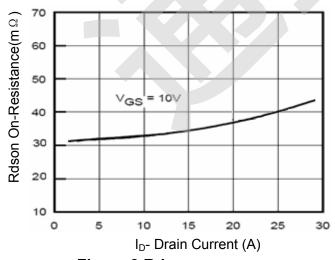


Figure 3 Rdson- Drain Current

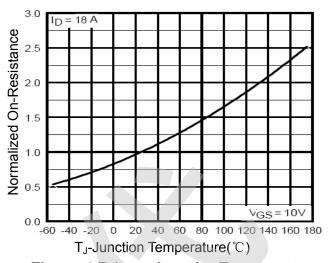


Figure 4 Rdson-JunctionTemperature

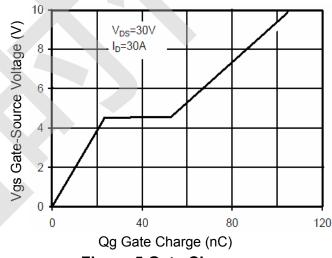


Figure 5 Gate Charge

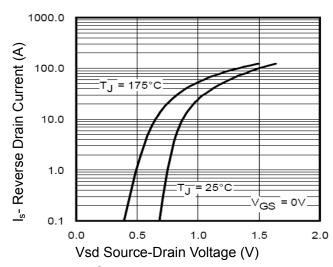


Figure 6 Source- Drain Diode Forward



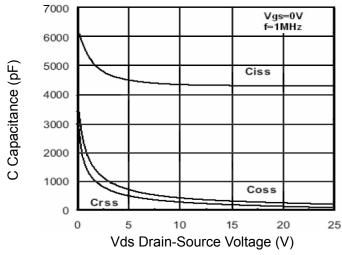


Figure 7 Capacitance vs Vds

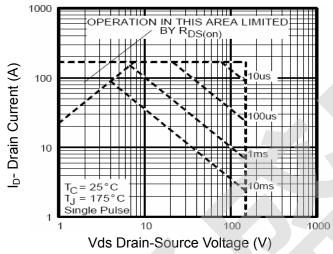


Figure 8 Safe Operation Area

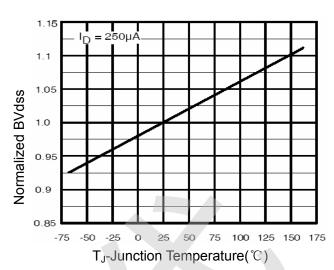


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

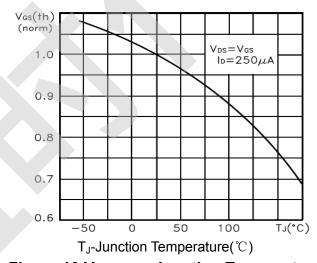
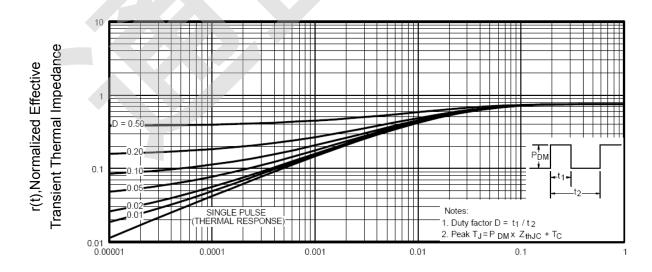


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

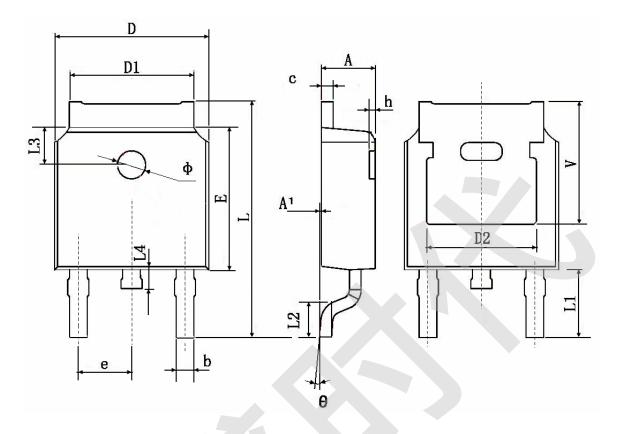


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



## **TO-252 Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
Α	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.8	30 TYP.	0.190	0.190 TYP.		
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	TYP.	0.114 TYP.			
L2	1.400	1.700	0.055	0.067		
L3	1.600	1.600 TYP. 0.063 TYP.				
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	5.350 TYP. 0.211 TYP.				



NCE1540K

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